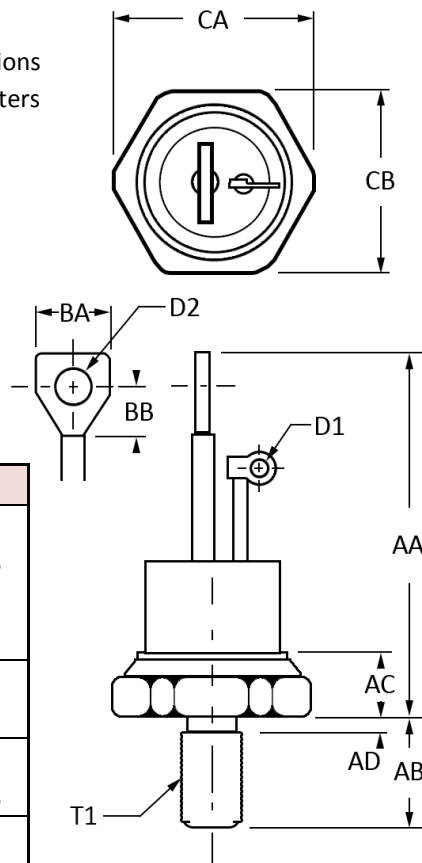




IMAGE SERVES AS A REPRESENTATION OF THE PACKAGE STYLE ONLY

## MECHANICAL SPECIFICATIONS

**Note:**  
All dimensions are in millimeters



	mm
AA	39.0 Max
AB	11.0 ± 0.5
AC	4.0 ± 0.5
AD	2.2 Max
BA	8.0
BB	4.0 Max
CA	21.0
CB	19.0 ± 0.3
D1	Ø1.8
D2	Ø3.6
T1	M6 x 1.0

## ABSTRACT

The 29RD60 is a general purpose p-n-p-n silicon control rectifier used primarily for switching. The thyristor is enclosed in a hermetically sealed NI-2 metal stud package, which contributes to the durability and longevity of the device.

## ELECTRICAL CHARACTERISTICS

V <sub>RSM</sub>	V <sub>RRM</sub>	I <sub>T(AV)</sub>		I <sub>TSM</sub> (50 Hz)	I <sup>2</sup> t t=2-10ms (A <sup>2</sup> S)	P <sub>GM</sub>	P <sub>G(AV)</sub>	V <sub>GRM</sub>	I <sub>GFM</sub>	T <sub>J</sub>	T <sub>stg</sub>	I <sub>RRM</sub> / I <sub>DRM</sub>	
		A	T <sub>C</sub> (°C)									(mA)	T <sub>J</sub> (°C)
700	600	26.0	88	500	1250.00	5.0	0.50	5.0	2.0	125	-40~125	10.0	125

V <sub>TM</sub>	T <sub>J</sub>		V <sub>GT</sub>	I <sub>GT</sub>	T <sub>C</sub>	V <sub>GD</sub> (min)			dv/dt (min)			I <sub>H</sub>	R <sub>th</sub>	Pkg.
	(V)	(°C)				(A)	(V)	T <sub>J</sub> (°C)	V <sub>D</sub> (V)	(V/μs)	T <sub>J</sub> (°C)			
1.92	25	80	2.5	50.00	25	0.20	125	2/3V <sub>DRM</sub>	200	125	2/3V <sub>DRM</sub>	70	0.8000	NI-2